

Title (en)
Integrated circuit devices and methods

Title (de)
Integrierte Schaltungen und Verfahren

Title (fr)
Dispositifs à circuit intégré et procédés

Publication
EP 2434493 A1 20120328 (EN)

Application
EP 10192904 A 20101129

Priority
US 38686310 P 20100927

Abstract (en)
An integrated circuit may include a plurality of first transistors organized into multiple groups, each group including a plurality of transistor rows, each first transistor varying current leakage in response to at least a first bias voltage applied to at least a first bias connection of the transistor; at least a first switch circuit corresponding to each group that applies at least the first bias voltage to at least all of the first bias connections of its corresponding group in response to an activation of a corresponding first select signal; and an activation circuit that activates less than all first select signals in response to an applied input value, and de-activates all first select signals in a default mode. Leakage current of SRAM groups can be reduced by selective application of source and well bias voltages to the groups.

IPC 8 full level
G11C 11/417 (2006.01)

CPC (source: EP)
G11C 11/413 (2013.01)

Citation (search report)

- [X] EP 1959452 A1 20080820 - ST MICROELECTRONICS INC [US]
- [X] US 2006133161 A1 20060622 - JACQUET FRANCOIS [FR], et al
- [X] US 2001038552 A1 20011108 - ISHIMARU KAZUNARI [JP]
- [X] US 2006098474 A1 20060511 - DANG LUAN [US], et al

Cited by
WO2014071049A3

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)
BA ME

DOCDB simple family (publication)
EP 2434493 A1 20120328; EP 2434494 A1 20120328

DOCDB simple family (application)
EP 10192904 A 20101129; EP 10192908 A 20101129